

# **ELEN E3106/4106 Lecture 13**

## **Optoelectronics Part II: LEDs and Lasers**

### **Outline**

- Light-emitting diodes
- Lasers
- Semiconductor lasers

#### **Assignments:**

Reading: Streetman and Banerjee §8.2-8.4

Homework 5 due tomorrow Friday Oct. 18<sup>th</sup> by 5pm

# Relationships between Optical Power, QE, Responsivity, and Photocurrent

- Recall, \_\_\_\_\_: optical generation rate of EHPs ( $\text{cm}^{-3}\text{s}^{-1}$ )
- $J_{op}$  or  $J_{ph}$ : Photocurrent density ( $\text{A}/\text{cm}^2$ )
- \_\_\_\_\_: Incident optical power or power density (\_\_\_\_ or  $\text{W}/\text{cm}^2$ )
- \_\_\_\_\_: Responsivity, photocurrent generated per incident optical power ( $\text{A}/\text{W}$ )

$$R = \frac{J_{op}}{P_0}$$

- $\eta_Q$ : External quantum efficiency (\_\_\_\_)

What is max  $\eta_Q$  if there is no gain mechanism (gain = 1)?

How many photons per unit area per second?

How many carriers per unit area per second do we collect?

Thus, we can write our QE:  $\eta_Q = (J_{op}/q)/(P_{op}/h\nu)$

# Vegard's Law for Alloys

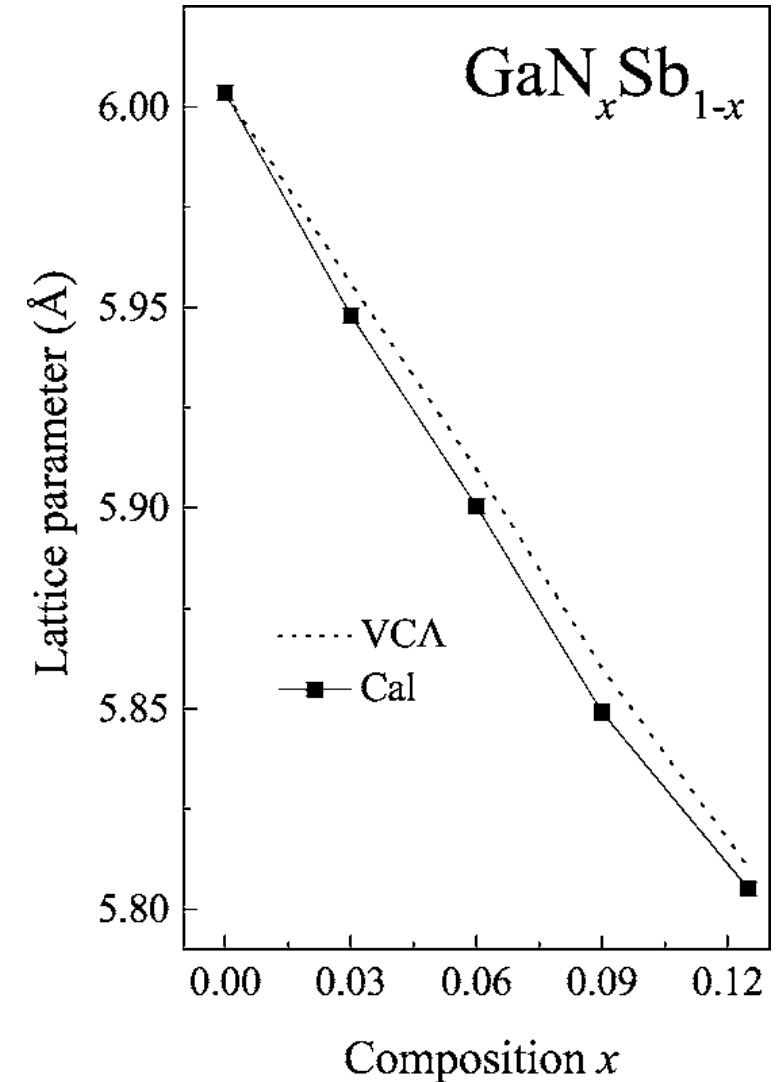
- Resembles the law of mixtures
- Lattice parameter, band gap are approximately weighted means of the constituents in an alloy:

$$a_{A(1-x)B_x} = (1 - x)a_A + xa_B$$

- Where  $x$  is the \_\_\_\_\_
- In many cases linear interpolation can be used to find the bandgap:

$$E_{g,E_{A(1-x)E_{B_x}}} = (1 - x)E_A + xE_B$$

- Ex.  $E_{g,Al_{0.8}GaN} = \text{_____} E_{g,AlN} + \text{_____} E_{g,GaN}$



## Example: p-i-n photodiode design

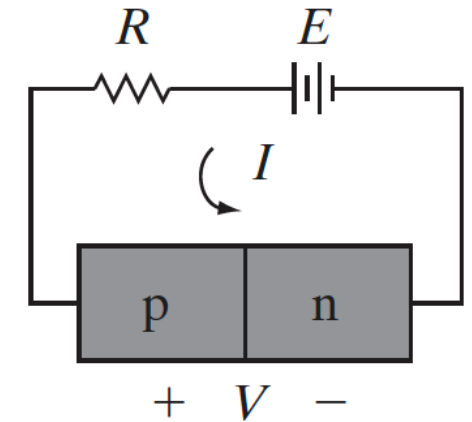
Consider a p-i-n photodiode with “i” region made of  $\text{In}_x\text{Ga}_{1-x}\text{As}$ . Design stoichiometry “x” and thickness of the “i” region ( $W_i$ ) to enable response at  $1.3\text{ }\mu\text{m}$  wavelength, up to 20 GHz signals. Assume fields are sufficiently high to reach  $v_{\text{sat}} \approx 10^7\text{ cm/s}$  in the “i” region. Name at least one design constraint on the “p” and “n” regions of this photodiode. You may assume the lattice constant and band gap of  $\text{In}_x\text{Ga}_{1-x}\text{As}$  vary linearly with composition “x”.

# LED Basics

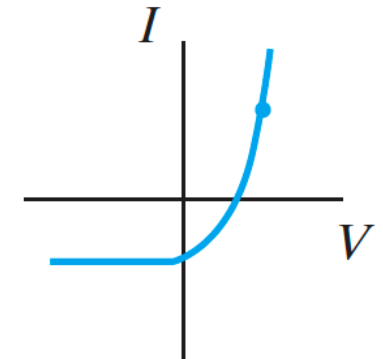
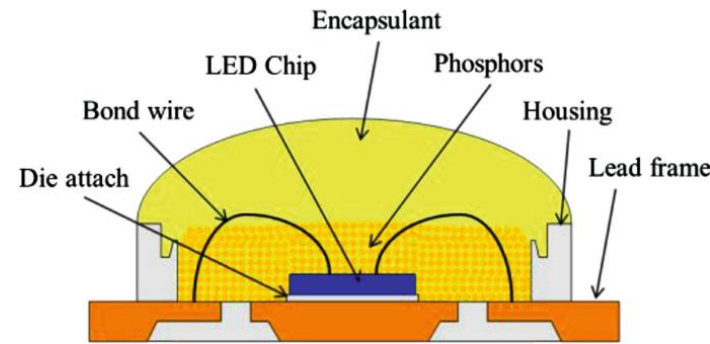
- Applications: displays, lighting, optical communications
- Convert electricity into \_\_\_\_\_
  - \_\_\_\_\_ quadrant
- \_\_\_\_\_ p-n junction
- What determines color of an LED?
  - \_\_\_\_\_!
  - Governed by Planck relation
  - Practically, phosphors are also used to alter LED color

$$E_g (\text{eV}) = 1.24/\lambda (\mu\text{m})$$

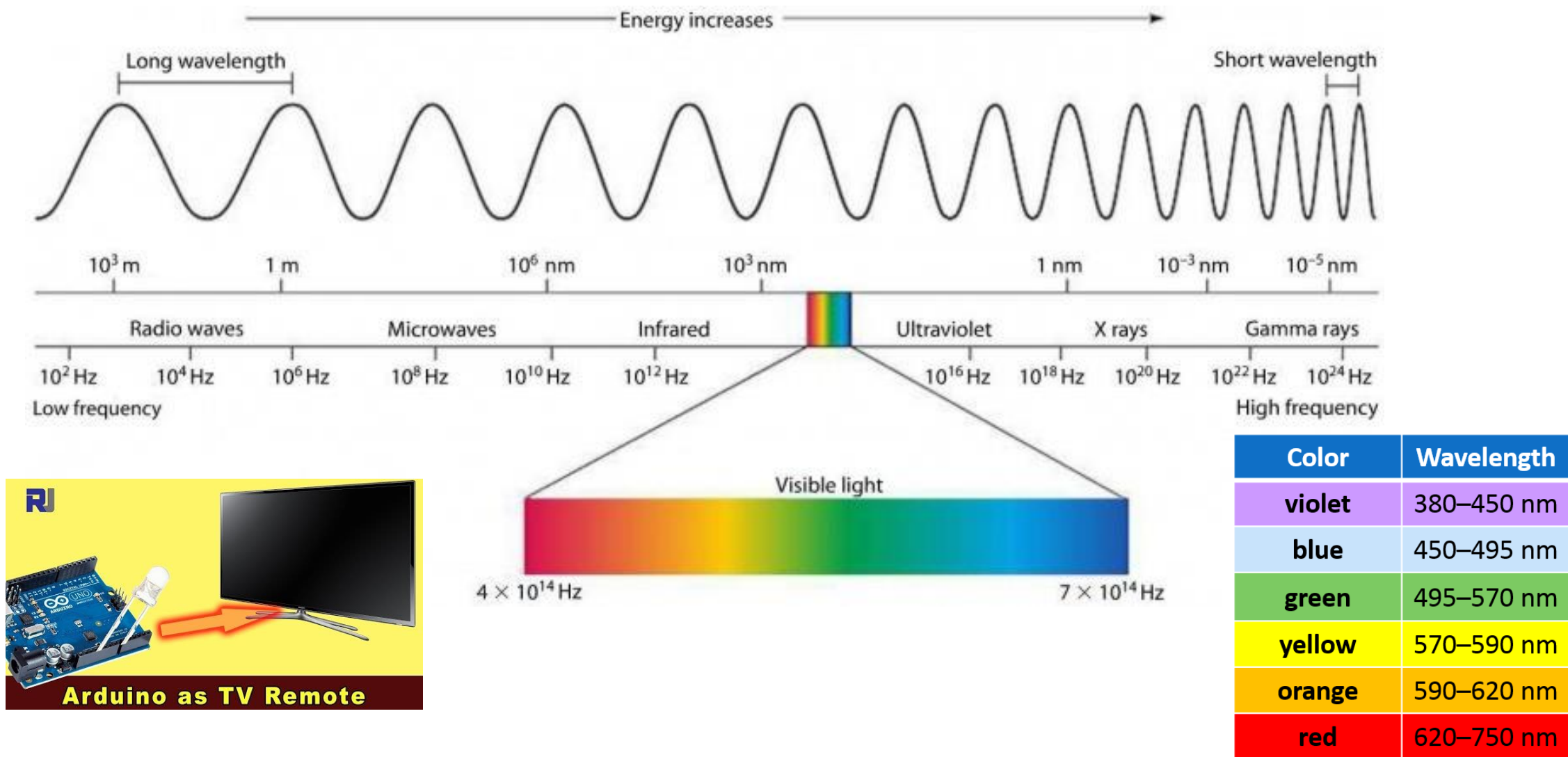
- How does the dome shape of an LED help extract for photons?



1st quadrant



# The Electromagnetic Spectrum



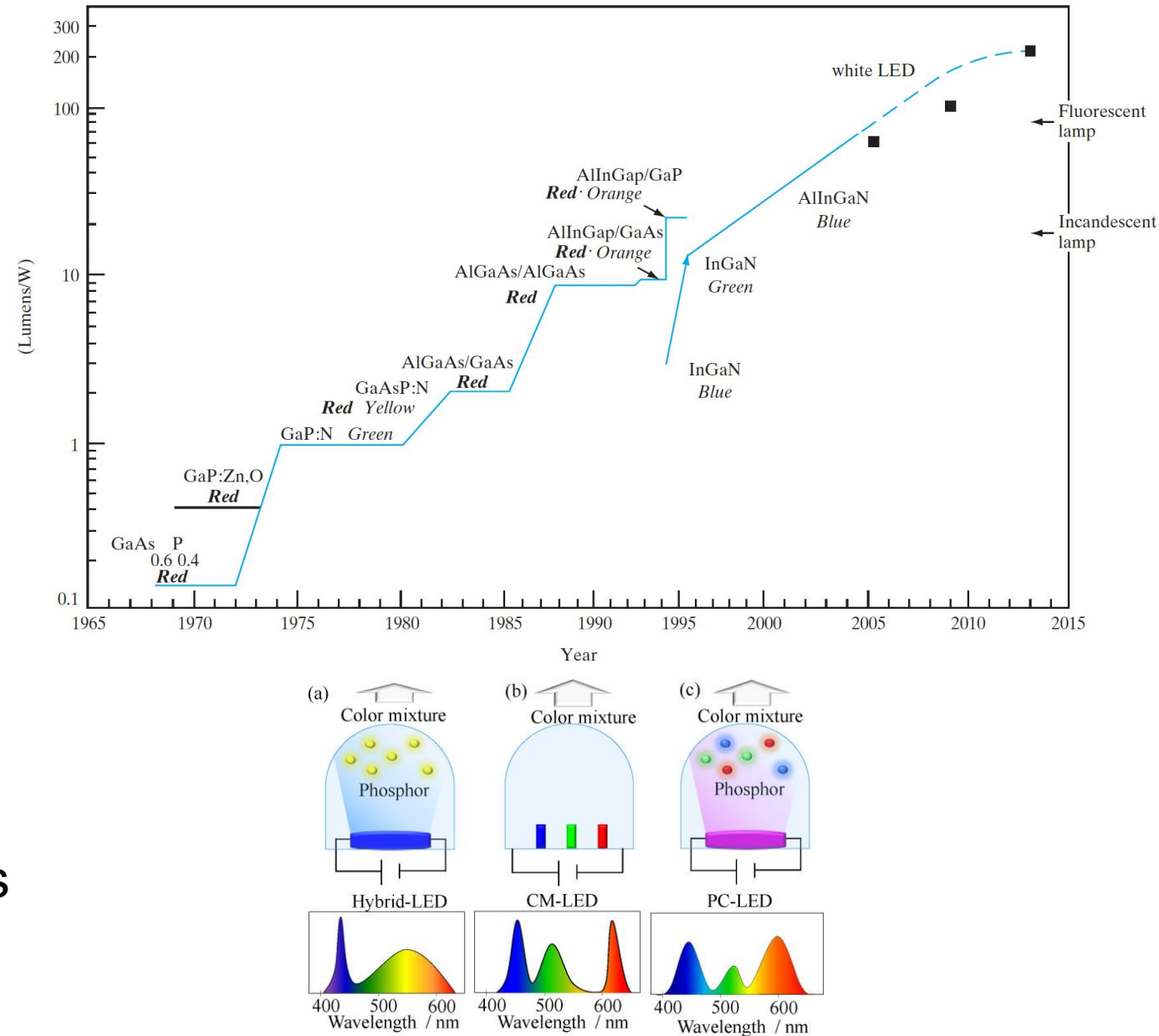
Sources: Principles of Structural Chemistry, Quora, Youtube

# Improvement in luminous intensity of LEDs over time

Luminous intensity: quantity of visible light that is emitted in \_\_\_\_\_ per \_\_\_\_\_

Why so much focus on developing green-blue LEDs?

Pros of LED over other lamps: longer lifetimes, much higher efficiencies, less breakable, cool to the touch (safety)



Sources: Textbook, <https://doi.org/10.1016/j.jlumin.2021.118167>

# LED Design

- Besides dome shape, how else do we increase photon extraction?
- Challenge: Heat dissipation!
  - Heat decreases \_\_\_\_\_
  - Need proper \_\_\_\_\_, like heat sinks
- Important: Low dislocation density crystals
  - Defects can cause \_\_\_\_\_, and decrease LED photon generation

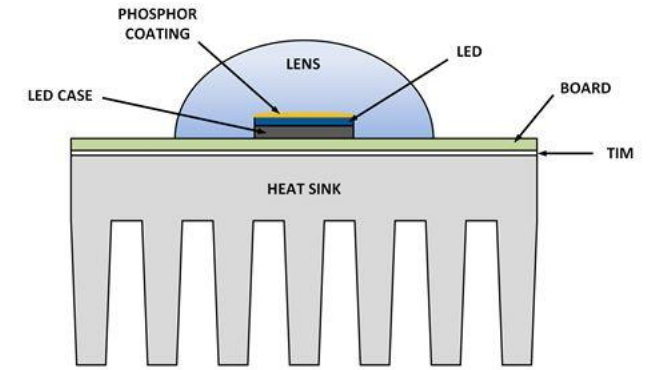
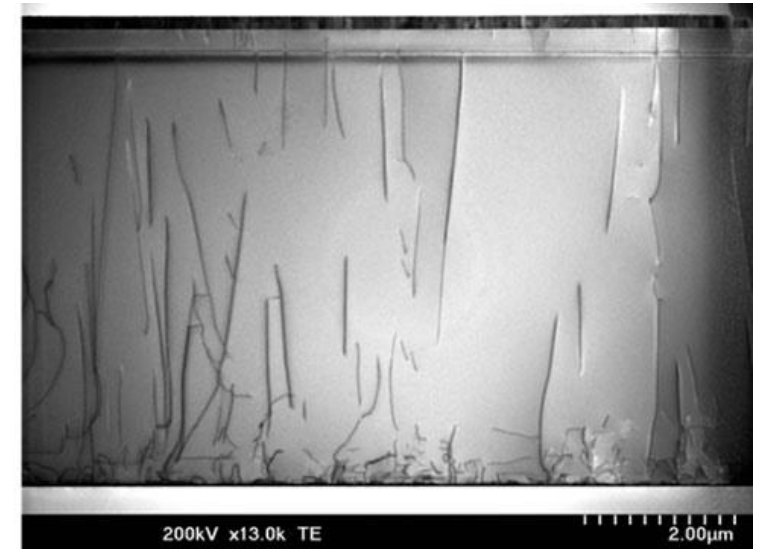


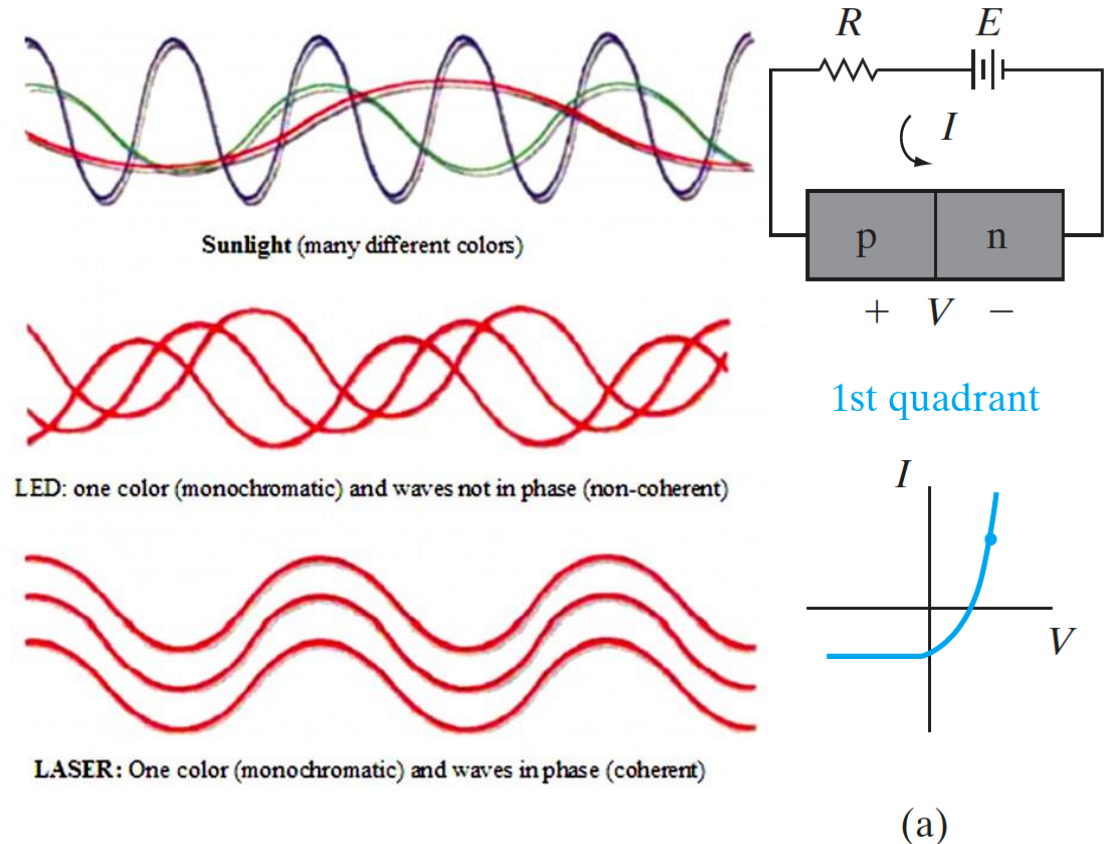
Figure 1 Diagram of the common elements of a LED light





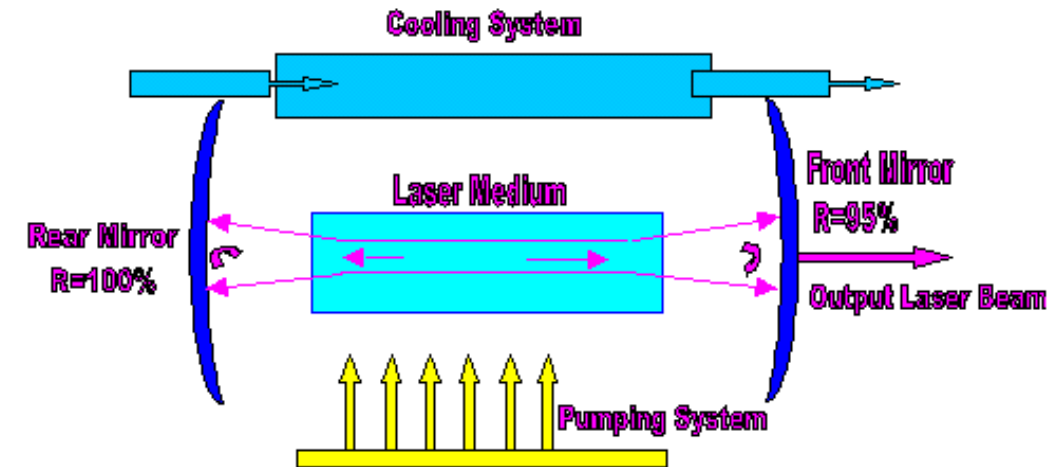
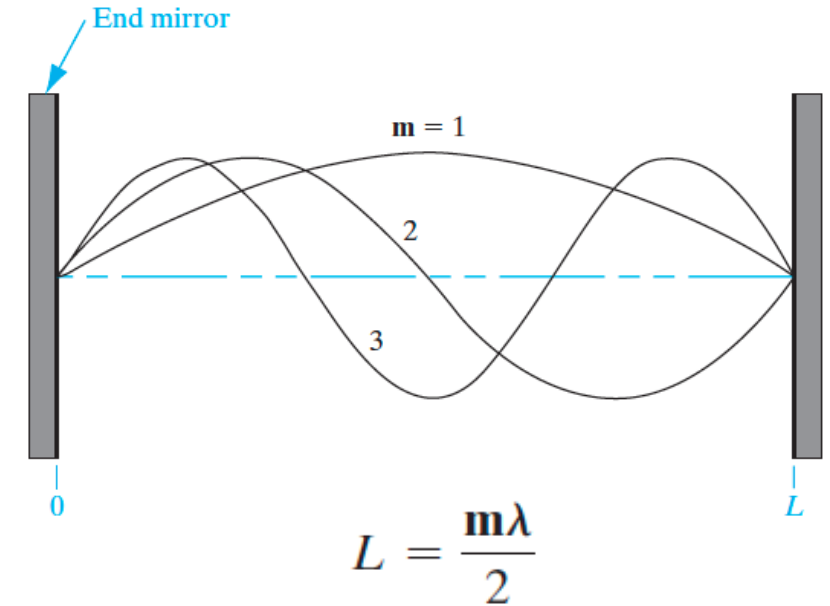
# Semiconductor Laser Basics

- Light **A**mplification by **S**timulated **E**mission of **R**adiation
- Laser light is:
  - Highly \_\_\_\_\_ I (unlike LED)
  - Coherent (photons are \_\_\_\_\_)
  - Monochromatic
- Pro of semiconductors over other laser types: small size, high efficiency, output easily modulated by junction current, low power)
- So far we have described *emission* (excited carriers randomly fall to lower energy states)
- How do we \_\_\_\_\_ emission?



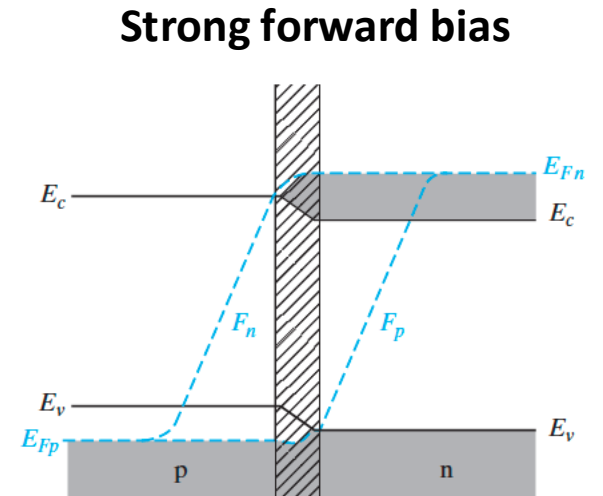
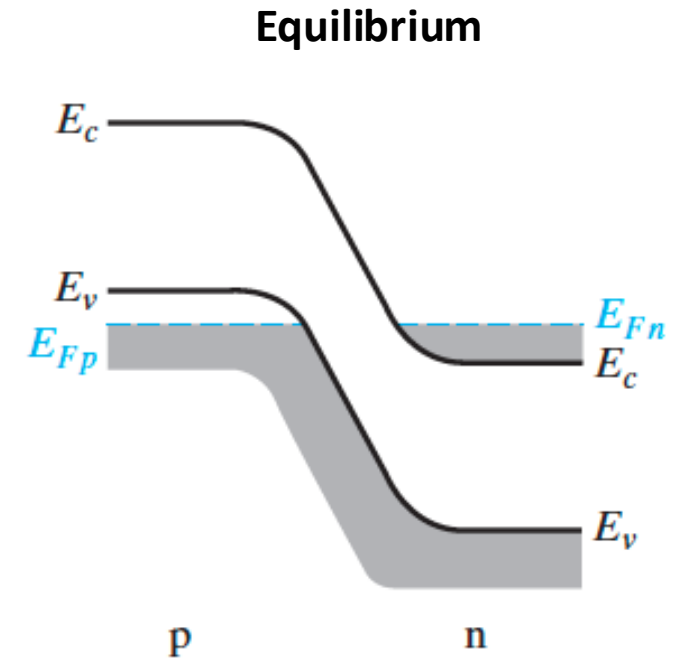
# Optical Cavities

- Conditions for photon density due to stimulated emission to dominate over spontaneous emission and absorption:
  1. **Optical resonant cavity to encourage photon field to build up**
  2. A means of obtaining \_\_\_\_\_
- Stimulated emission at  $\lambda = \frac{2L}{m}$  where m is an \_\_\_\_\_
- Parallel mirrors can provide multiple internal \_\_\_\_\_
- Fraction of light that “leaks out” of the resonant system is the output of the laser



# Population Inversion

- We can \_\_\_\_\_ *dope* semiconductors
  - $N_a, N_d$  very very high!
  - Fermi levels can move into the bands
  - Recall: Fermi level is the energy with 50% probability of being occupied!
- At strong forward bias, barrier is lowered -> many e- and h+ are \_\_\_\_\_ junction
- Instead of depleting junction region, we have a \_\_\_\_\_ population of carriers around the junction
- AKA there are more e- in the \_\_\_\_\_ band than in the valence band!
- If concentrations around junction are large enough, the condition of population inversion is met -> called \_\_\_\_\_



# Population Inversion Continued

- Our carrier concentrations can still be found as a function of \_\_\_\_\_:

$$n = N_c e^{-(E_c - F_n)/kT} = n_i e^{(F_n - E_i)/kT}$$

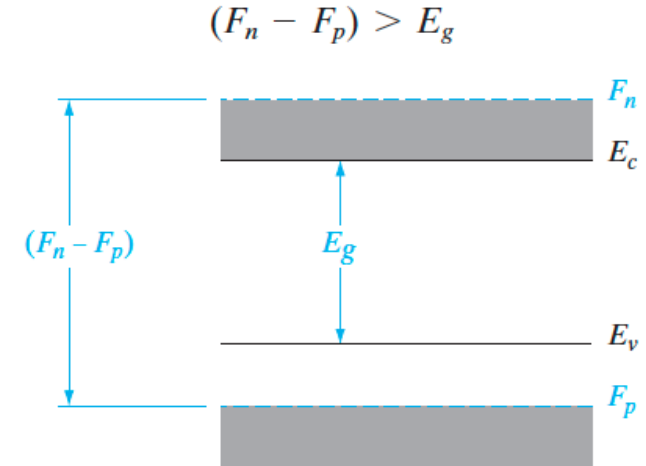
$$p = N_v e^{-(F_p - E_v)/kT} = n_i e^{(E_i - F_p)/kT}$$

- Where the \_\_\_\_\_ carrier concentration that allows for population inverse occurs when  $F_n - F_p = E_g$
- Normally a range of transition energies, from

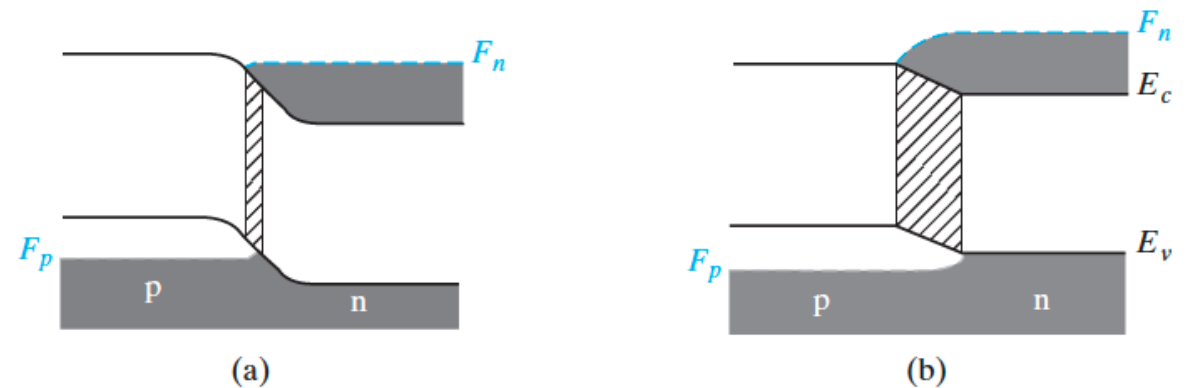
$$E_g < h\nu < (F_n - F_p)$$

- What does this mean for the emission spectra?

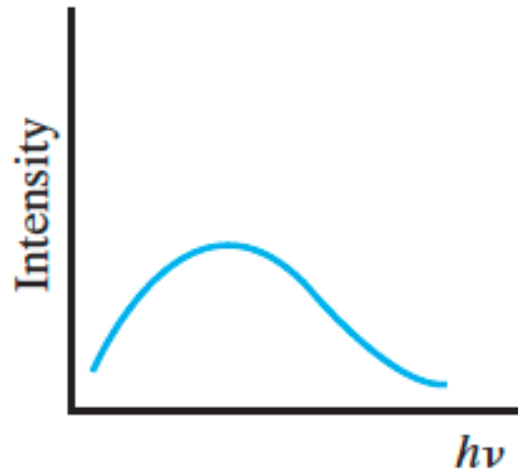
Condition for population inversion:



Variation of inversion-region width with forward bias  $V(a) < V(b)$ :



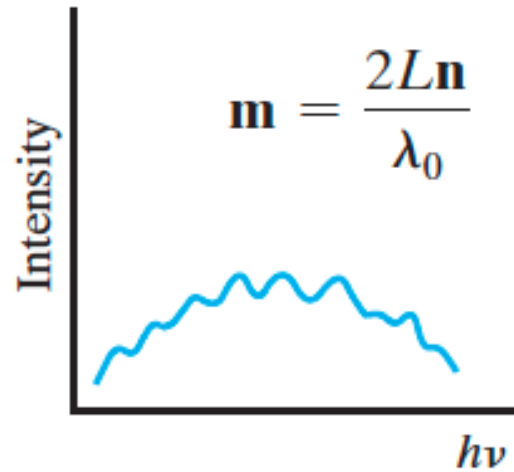
# Emission Spectra



(a)

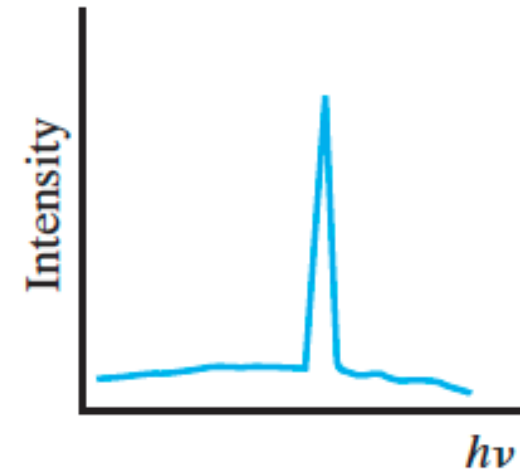
**Low forward bias:  
spontaneous emission  
between**

$$E_g < h\nu < (F_n - F_p)$$



(b)

**Increased forward bias:  
Significant pop. inversion.  
Stimulated emission  
occurs at cavity modes.**



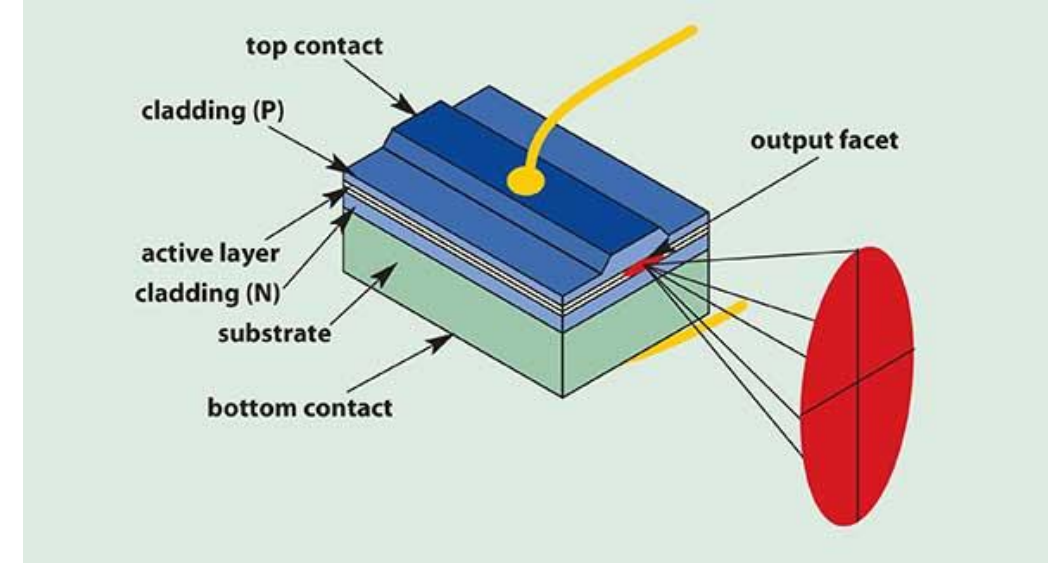
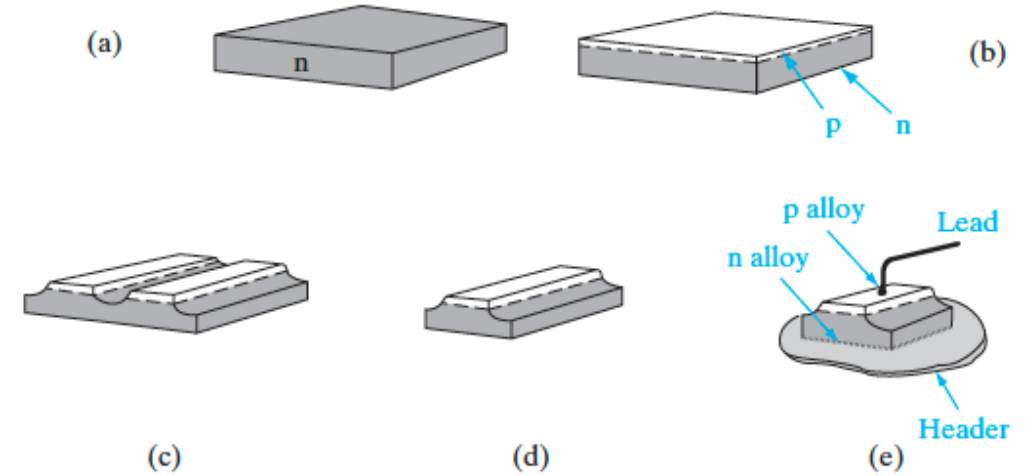
(c)

**Higher forward bias:  
Preferred mode will  
dominate and is the main  
laser output. Nearly  
monochromatic.**

- Question: what's the weak background “noise” in c?

# Semiconductor Laser Design and Fab

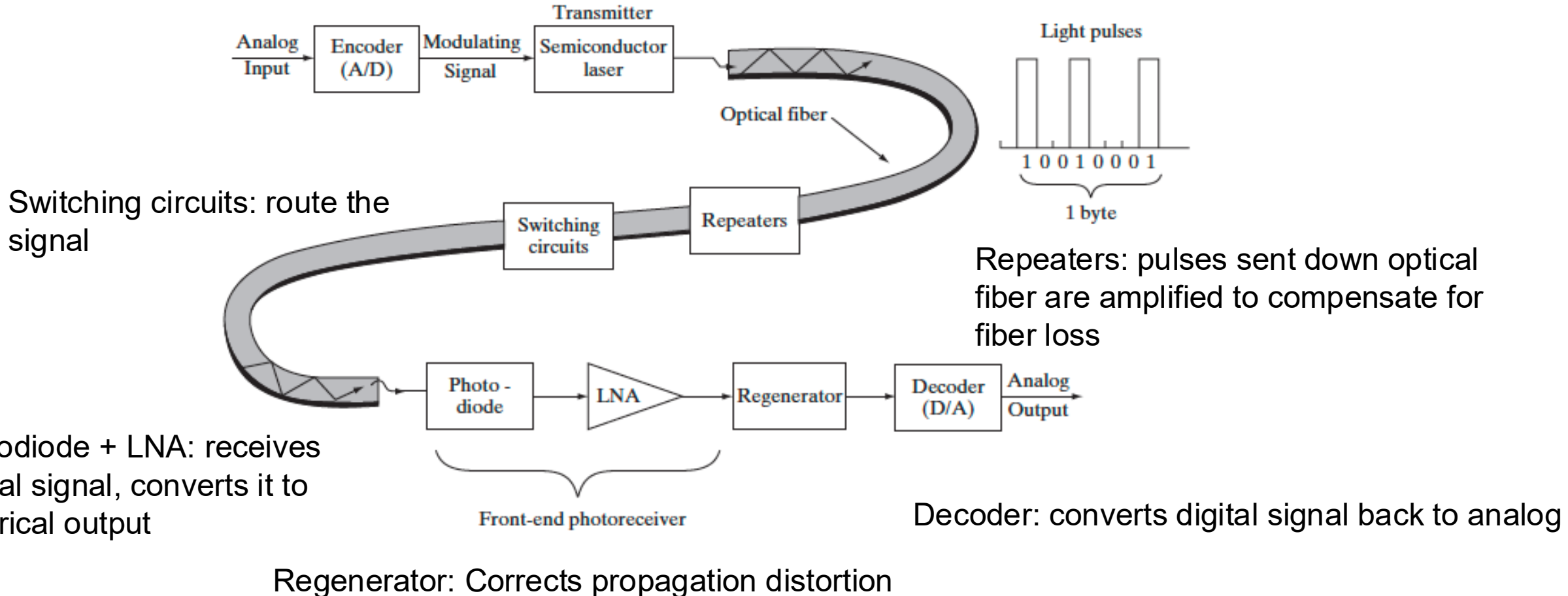
1. Form a \_\_\_\_\_ p-n junction, usually from a direct semi like GaAs
  2. Construct \_\_\_\_\_ with proper geometry (depends on junction)
  3. Make contact
  4. Design to allow for efficient heat transfer
- Important: front and back faces must be \_\_\_\_\_ and \_\_\_\_\_ (resonant cavity)
  - Heterojunctions, vertical cavity surface-emitting lasers (VCSELs) also popular



# Optoelectronics in Fiber Optics Communication

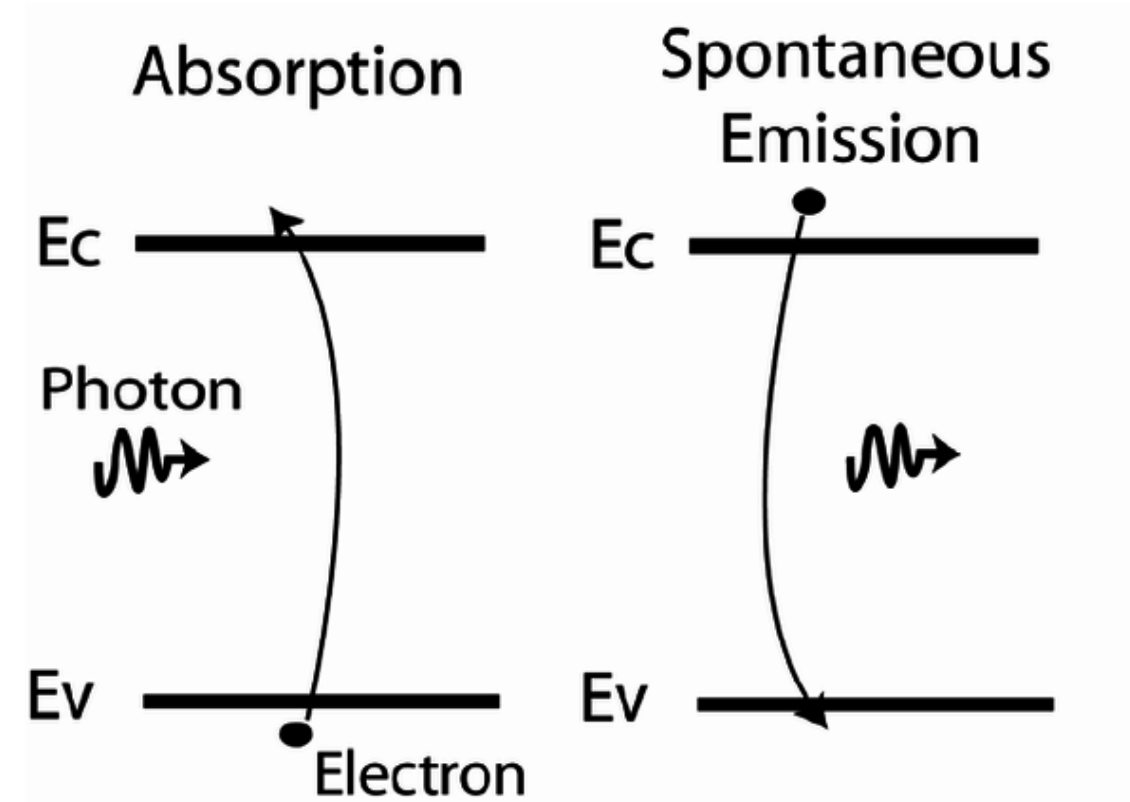
Encoder: Analog signal converted to digital signal

Transmitter: Digital signal modulates laser light as pulses



# Summary: Interaction of Light with Semiconductors

- Absorption: High probability that light (photons) with energy \_\_\_\_\_ are absorbed by the atoms.  $e^-$  are excited from \_\_\_\_\_ to \_\_\_\_\_
- Spontaneous emission: If atoms are in an excited state, spontaneous decay events cause  $e^-$  to “fall” from \_\_\_\_\_ to \_\_\_\_\_, and emit a photon with  $E$  \_\_\_\_\_





# Summary: Interaction of Light with Semiconductors

- e- already in the excited state can be agitated by the passage of a photon that has  $E$  \_\_\_\_\_. The excited e- relaxes to the ground state, e- "falls" from \_\_\_\_ to \_\_\_\_\_, and produces a **second photon** with energy \_\_\_\_\_
  - What happens to the original photon
  - Results: \_\_\_\_\_ photons of the same frequency are emitted (\_\_\_\_\_)
  - Population inversion is necessary condition, because it ensures that there are \_\_\_\_\_ e- in an excited state than in the ground state, allows for a \_\_\_\_\_ of photon emission

